



BSI Standards Publication

Semiconductor devices

Part 5-4: Optoelectronic devices — Semiconductor lasers

National foreword

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INTERNATIONAL STANDARD

AMENDMENT 1

**Semiconductor devices –
Part 5-4: Optoelectronic devices – Semiconductor lasers**

INTERNATIONAL
ELECTROTECHNICAL
COMMISSION

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CONTENTS

FOREWORD.....	4
INTRODUCTION.....	6
1 Scope.....	7
2 Normative references	7
3 Terms and definitions	7
3.1 Physical concepts	8
3.2 Types of devices	9
3.3 General terms	9
3.4 Terms related to ratings and characteristics.....	10
3.4.1 Switching times	10
3.4.2 Output and current characteristics	12
3.5 Spatial profiles and spectral characteristics	15
4 Essential rating and characteristics	15
4.1 Type	15
4.2 Semiconductor	15
4.2.1 Material	15
4.2.2 Structure	15
4.3 Details of outline drawing and encapsulation.....	16
4.4 Limiting values (absolute maximum ratings over the operating temperature range, unless otherwise stated)	16
4.5 Electrical and optical characteristics	16
4.6 Supplementary information	18
5 Measurement methods	18
5.1 Power measurement	18
5.2 Output stability.....	18
5.2.1 Relative intensity noise	18
5.2.2 Carrier-to-noise ratio	18
5.2.3 Output power stability	20
5.2.4 Output energy stability.....	20
5.2.5 Temporal pulse shape	20
5.3 Time domain profile	20
5.3.1 Switching times	20
5.3.2 Small signal cut-off frequency (f_c).....	22
5.4 Lifetime.....	22
5.5 Optical characteristics of the laser beam.....	23
5.5.1 Polarization	23
5.5.2 Half-intensity angle $\theta_{1/2}$ and $1/e^2$ -intensity angle θ_{1/e^2}	23
5.5.3 Half-intensity width $D_{1/2}$ and $1/e^2$ -intensity width D_{1/e^2}	25
5.5.4 Spectral characteristics and other spatial profile.....	26
Annex A (informative) Reference list of technical terms and definitions related to spatial profile and spectral characteristics.....	27
Annex B (informative) Reference list of measurement methods related to spatial profile and spectral characteristics.....	31
Annex C (informative) Reference list of technical terms and definitions, and measurement methods, related to power measurement and lifetime.....	32
Bibliography.....	

Figure 1 – Example of the device with window but without lens	10
Figure 2 – Switching times	12
Figure 3 – Threshold current of a laser diode	14
Figure 4 – Basic circuit diagram	19
Figure 5 – Basic circuits diagram	21
Figure 6 – Typical pulse response diagram	22
Figure 7 – Half-intensity angle	23
Figure 8 – Relationship between the specified plane and the mechanical reference plane	23
Figure 9 – Basic measurement setup diagram.....	24
Figure 10 – Measuring arrangement for $D_{1/2}$ and D_{1/e^2}	25
 Table 1 – Electrical and optical characteristics	 17

INTERNATIONAL ELECTROTECHNICAL COMMISSION

SEMICONDUCTOR DEVICES –

**Part 5-4: Optoelectronic devices –
Semiconductor lasers**

FOREWORD

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IEC 60747-5-4 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices. It is an International Standard.

This second edition cancels and replaces the first edition published in 2006. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) References for the terms and definitions related to the lighting area, IEC 60050-845, are revised based on IEC 60050-845:2020;
- b) Emission angle is changed to radiation angle in 3.3.2;
- c) Definitions of rise time and fall time in 3.4.1 are revised based on the publication IEC 60050-521:2002;
- d) Spectral linewidth is added to Table 1 in Clause 4;
- e) Conditions for carrier-to-noise ratio of Table 1 in Clause 4 is amended.

- f) Error in the equation for carrier-to-noise ratio in 5.2.2 is corrected;
- g) Precaution against the equipment used for carrier-to-noise ratio measurement is added in 5.2.2;
- h) Explanation for the measurement method of the small signal cut-off frequency in 5.3.2 of the first edition is deleted because it has been defined in the latest version of ISO 11554;
- i) Reference document for the lifetime in 5.4 is amended;
- j) Precaution against the measuring arrangement used for the half-intensity width and $1/e^2$ -intensity is added in 5.5.3;
- k) Reference tables in Annex A, Annex B and Annex C are revised by following the latest version of ISO publications.

The text of this International Standard is based on the following documents:

Draft	Report on voting
47E/783/FDIS	47E/785/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/standardsdev/publications.

A list of all parts in the IEC 60747 series, published under the general title *Semiconductor devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

INTRODUCTION

The first edition of this part of IEC 60747 was published in 2006 under close collaboration between IEC TC 47 SC 47E (IEC TC 47 SC 47C at that moment) and ISO TC 172 SC 9. The scope of IEC/TC47/SC47E includes laser diodes as one of the discrete semiconductor devices while that of ISO/TC172/SC9 includes laser diodes as one of the laser and laser-related equipment. Consequently, technical contents in this publication extend over IEC and ISO.

In order to harmonize the IEC and ISO laser-related standards in 1997, a joint working group (JWG) consisted of the experts from both IEC SC 47E and ISO TC 172 SC 9 was established. As a result of discussion, items based on the electrical and electronic technologies are dealt with by subcommittee 47E of IEC technical committee 47, while optical characteristics of the output beam are under the responsibility of subcommittee 9 of ISO technical committee 172. This was agreed, after long discussion, in 2002 between subcommittee 47E of IEC technical committee 47 and subcommittee 9 of ISO technical committee 172. Based on this agreement, terms and definitions, and test and measurement methods for the optical beam parameters in this part of IEC 60747-5-4 are referenced to the ISO standards that specify the topics.

The joint working group was disbanded in 2017. However, close co-operation and contact between two groups is indispensable in order to avoid any conflicts and to keep harmonization of IEC and ISO laser standards.

This second edition of IEC 60747-5-4 has been updated by following the revision and amendments in the latest versions of laser standards of both IEC and ISO.

SEMICONDUCTOR DEVICES –

Part 5-4: Optoelectronic devices – Semiconductor lasers

1 Scope

This part of IEC 60747 specifies the terminology, the essential ratings and characteristics as well as the measuring methods of semiconductor lasers.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC TR 62572-2, *Fibre optic active components and devices – Reliability standards – Part 2: Laser module degradation*

ISO 11146-1, *Lasers and laser-related equipment – Test methods for laser beam widths, divergence angles and beam propagation ratios – Part 1: Stigmatic and simple astigmatic beams*

ISO 11554, *Optics and photonics – Lasers and laser-related equipment – Test methods for laser beam power, energy and temporal characteristics*

ISO 12005, *Lasers and laser-related equipment – Test methods for laser beam parameters – Polarization*

ISO 17526, *Optics and optical instruments – Lasers and laser-related equipment – Lifetime of lasers*

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

3.1 Physical concepts

3.1.1

electromagnetic radiation, <phenomenon>

phenomenon by which energy in the form of electromagnetic waves or photons emanates from a source and is transferred through space

Note 1 to entry: The term "electromagnetic radiation" is also used for the electromagnetic waves or photons produced (see IEC 705-02-01).

Note 2 to entry: The physical concepts of photons and electromagnetic waves are used to describe the same phenomenon of transmission of radiant energy in different ways, depending on the nature of the interaction of the energy with the physical world (wave-particle dualism).

[SOURCE: IEC 60050-702:1992/AMD5:2019, 702-02-07]

3.1.2

electromagnetic radiation, <waves or photons>

energy that emanates from a source in the form of electromagnetic waves or photons and is transferred through space

Note 1 to entry: The term "electromagnetic radiation" is also used for the phenomenon producing the electromagnetic waves or photons (see IEC 702-02-07).

Note 2 to entry: The physical concepts of photons and electromagnetic waves are used to describe the same phenomenon of transmission of radiant energy in different ways, depending on the nature of the interaction of the energy with the physical world (wave-particle dualism).

[SOURCE: IEC 60050-705:1995/AMD4:2019, 705-02-01]

3.1.3

optical radiation

electromagnetic radiation at wavelengths between the region of transition to X-rays ($\lambda \approx 1$ nm) and the region of transition to radio waves ($\lambda \approx 1$ mm)

Note 1 to entry: This entry was numbered 845-01-02 in IEC 60050-845:1987.

[SOURCE: IEC 60050-845:2020, 845-21-002]

3.1.4

light, <psychophysical> noun

radiation that is considered from the point of view of its ability to excite the visual system

Note 1 to entry: The term "light" is sometimes used for optical radiation extending outside the visible range, but this usage is not recommended.

Note 2 to entry: This entry was numbered 845-01-06 in IEC 60050-845:1987.

[SOURCE: IEC 60050-845:2020, 845-21-012]

3.1.5

light, <photometric> noun

radiation within the spectral range of visible radiation

Note 1 to entry: Sometimes, the term "light" is also used in physics as a synonym of optical radiation, covering the spectral range from 100 nm to 1 mm and sometimes even covering the X-ray spectral range. This misuse of the term "light" should be avoided.

[SOURCE: IEC 60050-845:2020, 845-21-013]

3.1.6

visible radiation

optical radiation (IEV 845-21-002) capable of causing a visual sensation directly

Note 1 to entry: There are no precise limits for the spectral range of visible radiation since they depend upon the amount of radiant flux reaching the retina and the responsivity of the observer. The lower limit is generally taken between 360 nm and 400 nm and the upper limit between 760 nm and 830 nm.

Note 2 to entry: This entry was numbered 845-01-03 in IEC 60050-845:1987.

Note 3 to entry: ISO 20473:2007 Optics and photonics – Spectral bands defines from 380 nm to 780 nm for the range of visible radiation.

[SOURCE: IEC 60050-845:2020, 845-021-003, modified – Note 3 has been added.]

3.2 Types of devices

3.2.1

semiconductor laser

laser diode

semiconductor diode that emits coherent optical radiation through stimulated emission resulting from the recombination of conduction electrons and holes when excited by an electric current that exceeds the threshold current of the diode

Note 1 to entry: The laser diode is mounted on a submount or in a package with or without coupling means (e.g. lens, fibre pigtail).

[SOURCE: IEC 60050-521:2002, 521-04-37, modified – The term "laser diode" has been replaced by "semiconductor laser".]

3.3 General terms

3.3.1

beam axis

straight line connecting the centroids defined by the first spatial moments of the cross-sectional power (energy) density distribution function at successive locations in the direction of propagation (z) of the beam in a homogeneous medium

[SOURCE: ISO 11145:2018, 3.2.1]

3.3.2

optical port

geometrical configuration, referenced to an external plane or surface of the device, that is used to specify the optical radiation emitted from an emitting device

EXAMPLE

Signification of annotations in the Figure 1:

α = acceptance angle or radiation angle



= optical port with diameter D

Ref. = reference locus for the definition of the optical port